

a 2004 0033

The invention relates to the technology of semiconductor materials and may be used for cleaning of machining attachments from waste after epitaxial growth of semiconductor layers of gallium arsenide or indium phosphide.

The process for cleaning of machining attachments from waste after epitaxial growth of semiconductor layers of the type  $A^3B^5$  includes the chemical treatment of the machining attachments part with waste by submergence into a vessel filled with acid solution, containing a mixture of nitric acid  $HNO_3$  and hydrochloric acid  $HCl$ , subsequent washing thereof with deionized water and drying. The chemical treatment is carried out with acid solution, containing 25...52 vol.% of nitric acid  $HNO_3$ . The acid solution is preliminarily degasified during 1,5...4 hours in deionized water.

Claims: 2

Fig.: 2